

Customer No.: 31561
Docket No.: 13794-US-PA
Application No.: 10/711,160

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AMENDMENT

To the Specification

[Para 16] On the other hand, the transparent end portions 210a of the isolated line patterns 210 and the transparent phase-shift region 230 may be recessed portions of the substrate 200, wherein the ~~π -shift~~ π -shift end portion 210a of an isolated line pattern 210 is ~~recess~~ recessed more than the ~~$\pi/2$ -shift~~ $\pi/2$ -shift region 230.

[Para 20] It is noted that though the line patterns are arranged in pairs in an end-to-end manner within the above embodiment, a single isolated line pattern having a transparent ~~π -shift~~ π -shift end portion, or a single group of dense line patterns with a transparent ~~$\pi/2$ -shift~~ $\pi/2$ -shift region adjacent to their ends, can also reduce the LES effect. Moreover, this invention not only is applicable to a photomask with isolated/dense line patterns thereon as in the above embodiment, but also can be applied to a photomask with other[[type]] types of isolated/dense linear patterns thereon. In addition, the photomask of this invention may include merely isolated line patterns each having a transparent ~~π -shift~~ π -shift end portion, or merely dense line patterns with a transparent ~~$\pi/2$ -shift~~ $\pi/2$ -shift region adjacent to their ends.